MOSFET – Single P-Channel, Small Signal, XDFN3, 0.62 x 0.42 x 0.4 mm -20 V, -127 mA

• Low Profile Ultra Small Package, XDFN3 (0.62 x 0.42 x 0.4 mm)

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS



ON Semiconductor®

www.onsemi.com

V _{(BR)DSS}	R _{DS(on)} MAX	I _D Max
	5.0 Ω @ –4.5 V	
	5.5 Ω @ –3.3 V	
–20 V	6.0 Ω @ –2.5 V	–127 mA
	7.0 Ω @ –1.8 V	
	10 Ω @ –1.5 V	

Applications

Compliant

• -1.5 V Gate Drive

Features

- Small Signal Load Switch
- High Speed Interfacing
- Level Shift

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise stated)

for Extremely Space-Constrained Applications

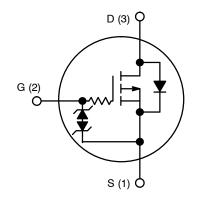
(,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,					
Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain	Steady	$T_A = 25^{\circ}C$	Ι _D	-127	mA
Current (Note 1)	State	$T_A = 85^{\circ}C$		-91	
	t ≤ 5 s	$T_A = 25^{\circ}C$		-146	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}C$	PD	125	mW
	t ≤ 5 s			166	
Pulsed Drain Current	t _p = 10 μs		I _{DM}	-488	mA
Operating Junction and Storage Temperature		T _J , T _{STG}	–55 to 150	°C	
Source Current (Body Diode) (Note 2)			۱ _S	200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		ΤL	260	°C	
0			Dell's secondate		

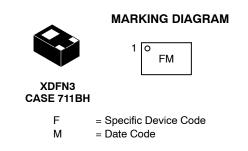
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

P-CHANNEL MOSFET





ORDERING INFORMATION

Device	Package	Shipping [†]
NTNS5K0P021ZTCG	XDFN3 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit	
Junction-to-Ambient - Steady State (Note 3)	R_{\thetaJA}	998	°C/W	
Junction-to-Ambient – t \leq 5 s (Note 3)	R_{\thetaJA}	751	C/VV	

3. Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -25 \text{ V}$	i0 μA	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V_{GS} = 0 V, V_{DS} = -5 V	$T_J = 25^{\circ}C$			-50	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V, V_{DS} = -16 V$ $T_{J} = 25^{\circ}C$				-100	nA
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±5 V				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = -2$	50 μA	-0.4		-1.0	V
Drain-to-Source On Resistance		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -100 \text{ mA}$			2.1	5.0	Ω
	R _{DS(on)}	V _{GS} = -3.3 V, I _D = -100 mA			2.4	5.5	
		$V_{GS} = -2.5 \text{ V}, I_D = -50 \text{ mA}$			2.7	6.0	
		$V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$			3.6	7.0	
		V _{GS} = -1.5 V, I _D = -10 mA			4.2	10	
Forward Transconductance	g fs	$V_{DS} = -5 \text{ V}, \text{ I}_{D} = -125 \text{ mA}$			0.35		S
Source-Drain Diode Voltage	V _{SD}	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = -10 \text{ mA}$			-0.6	-1.0	V
CHARGES & CAPACITANCES							
Input Capacitance	C _{ISS}				12.8		
Output Capacitance	C _{OSS}	V_{GS} = 0 V, freq = 1 MHz, V_{DS} = –15 V			2.8		pF
Reverse Transfer Capacitance	C _{RSS}				2.0		
SWITCHING CHARACTERISTICS, VG	S = 4.5 V (Not	e 4)					
Turn-On Delay Time	t _{d(ON)}				37		
Rise Time	t _r	- V _{GS} = -4.5 V. V _{DD} = -15 V.			71		_
Turn-Off Delay Time	t _{d(OFF)}	V_{GS} = -4.5 V, V_{DD} = -15 V, I_D = 200 mA, R_G = 2 Ω			280		ns

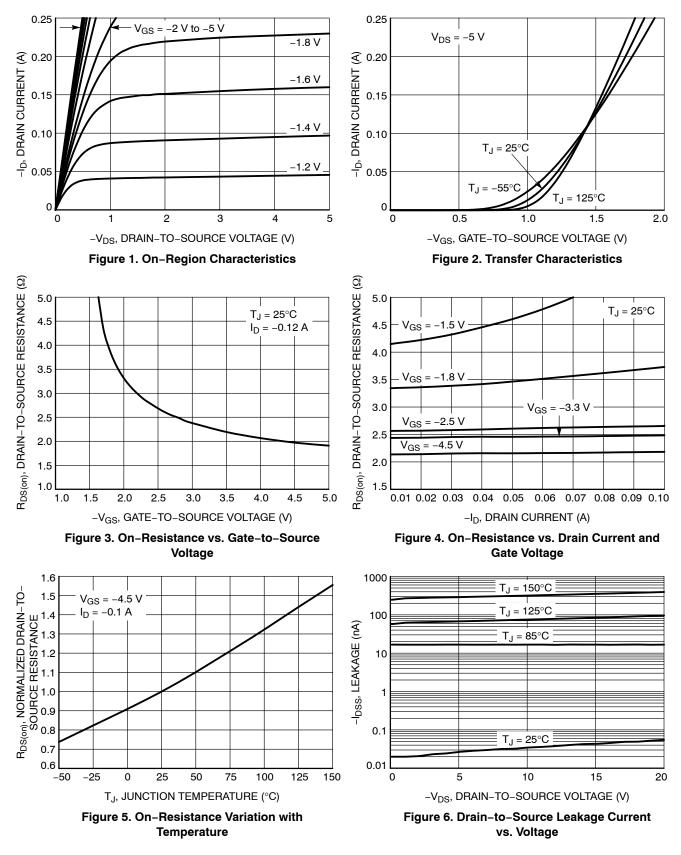
171

4. Switching characteristics are independent of operating junction temperatures.

t_f

Fall Time

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

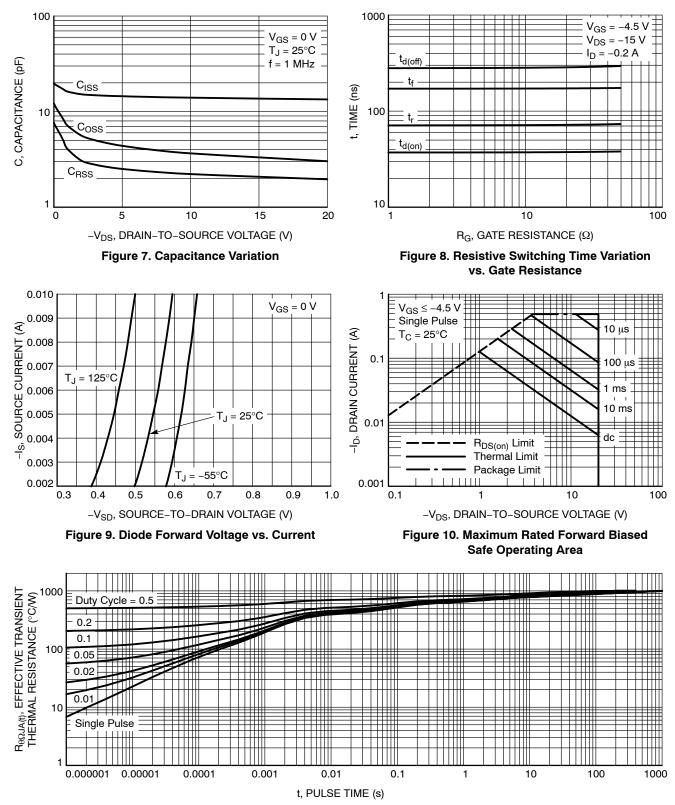
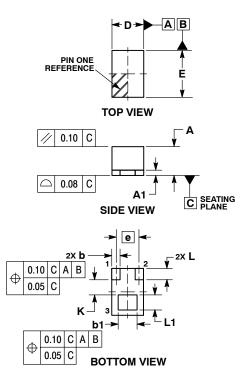


Figure 11. Thermal Response

PACKAGE DIMENSIONS

XDFN3 0.42x0.62, 0.3P CASE 711BH **ISSUE O**

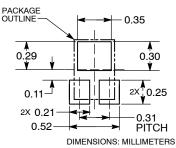


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2 CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION 6 AND 61 APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.20 AND 0.25MM FROM THE TERMINAL TIP.
- 4.
- COPLANARITY APPLIES TO THE PLATED TERMI-NALS

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.33	0.38	0.43	
A1			0.07	
b	0.05	0.11	0.17	
b1	0.20	0.25	0.30	
D	0.32	0.42	0.52	
Е	0.52	0.62	0.72	
е	0.30 BSC			
L	0.09	0.15	0.21	
L1	0.15	0.20	0.25	
K	0.20 REF			

RECOMMENDED SOLDER FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and we trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

Phone: 421 33 790 2910

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative